

Description

The XT3D24VU TVS diode is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebooks, and PDA's. It offers superior electrical characteristics such as low clamping voltage, low leakage current and high surge capability. It is designed to protect sensitive electronic components which are connected to power lines, from over-stress caused by ESD (Electrostatic Discharge), EFT (Electrical Fast Transients) and Lightning.

The XT3D24VU is in a SOD-323 package and will protect one unidirectional line. It may be used to provide ESD protection up to $\pm 30 \text{kV}$ (Contact and air discharge) according to IEC61000-4-2 , and withstand peak pulse current up to 80A (8/20 us) according to IEC61000-4-5.

Features

- Working voltage: 24V
- ◆ SOD323 Package
- ◆ 2400 Watts peak pulse power (t_p=8/20us)
- ◆ Transient protection for data lines to IEC 61000-4-2 (ESD) ±30kV (air), ±30kV (contact)

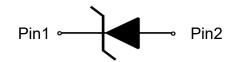
IEC 61000-4-5 (Surge) 80A (8/20us) IEC61000-4-4(EFT)40A(5/50ns)

- ◆ Low leakage current
- Low clamping voltage
- Solid-state silicon-avalanche technology

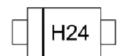
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SOD-323



Circuit Diagram



Marking

Order Information

Device	Package	Shipping
XT3D24VU	SOD-323	3000/Tape&Reel

Applications

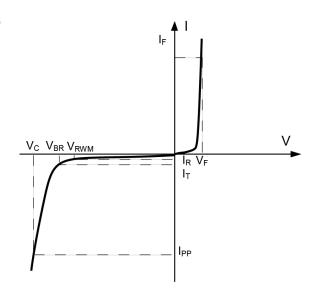
- Power lines
- Personal digital assistants (PDA's)
- Microprocessors based equipment
- Notebooks, Desktops, and Servers
- Cell phone Handsets and Accessories
- Portable Electronics
- Peripherals

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Definitions of electrical characteristics

Symbol	Parameter		
V _{RWM}	Reverse Stand-off Voltage		
IR	Reverse Leakage Current @ V _{RWM}		
V_{BR}	Reverse Breakdown Voltage @ I _T		
Ι _Τ	Test Current		
I _{PP}	Reverse Peak Pulse Current		
Vc	Clamping Voltage @ I _{PP}		
lF	Forward Current		
VF	Forward Voltage @ I _F		
Cj	Junction Capacitance		
I _{PP}	Peak Pulse Current		



Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power (t _P = 8/20μS)	РРК	2400	W
Peak Pulse Current (t _P = 8/20µS)	lpp	80	А
ESD according to IEC61000-4-2 air discharge	V	±30	kV
ESD according to IEC61000-4-2 contact discharge	Vesd	±30	kV
Lead Soldering Temperature	T∟	260 (10 sec)	°C
Operating Temperature	T _{OP}	-55 to +125	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Electrical Characteristics (Ta=25 $^{\circ}$ C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Reverse Stand-off Voltage	V _{RWM}				24	٧
Reverse Breakdown Voltage	V_{BR}	I _T =1mA	26	27	31.5	٧
Reverse Leakage Current	I _R	V _{RWM} =24V			1	μΑ
Clamping Voltage	Vc	I _{PP} =80A t _P = 8/20μs		30	33	٧
Junction Capacitance	Cj	V _R =0V f = 1MHz		230	400	pF



Typical Characteristics (Ta=25℃, unless otherwise noted)

FIG.1:V- I curve characteristics (Uni-directional)

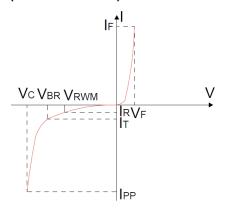


FIG.3: Pulse derating curve

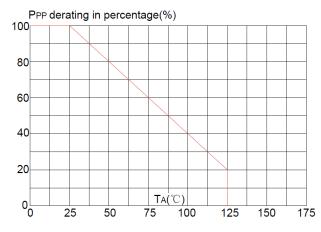


FIG.2: Pulse waveform (8/20µs)

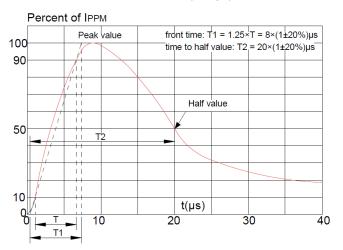
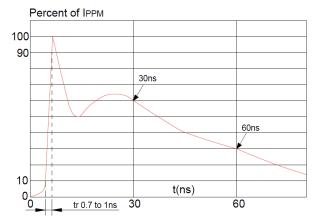
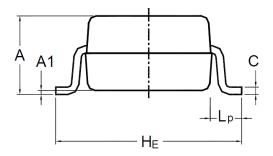


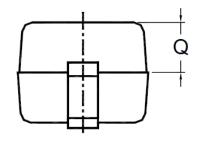
FIG.4: ESD clamping (30kV contact)

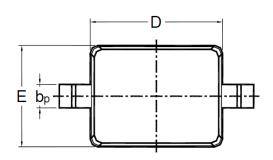




Package Outline Dimensions (SOD-323)

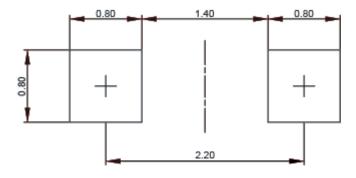






Dim	Inches		Millimeters		
	MIN	MAX	MIN	MAX	
Α	0.031	0.043	0.8	1.0	
A ₁	0.000	0.004	0	0.1	
b _p	0.010	0.016	0.25	0.4	
С	0.000	0.006	0	0.15	
D	0.063	0.071	1.6	1.8	
E	0.045	0.053	1.15	1.35	
HE	0.091	0.110	2.3	2.8	
L _P	0.004	0.020	0.1	0.5	
Q	0.012	0.020	0.3	0.5	

Recommend Land Pattern (Unit: mm)

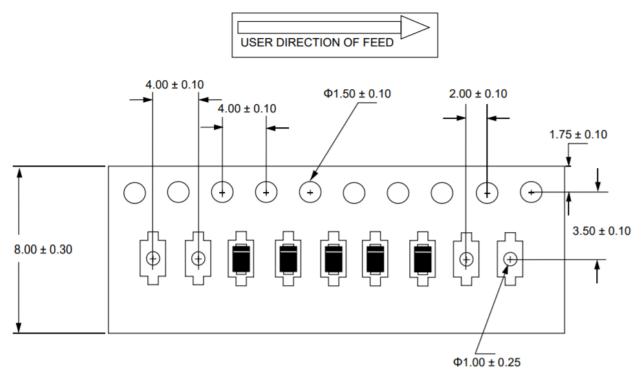


Note:

This recommended land pattern is for reference purpose only.



Load With Information



Unit: mm

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